Thermal Al_2O_3 Atomic Layer Etching Using HF and Hacac Reactants: Etch Enhancement from Refluorination by Product HF During Hacac Reaction

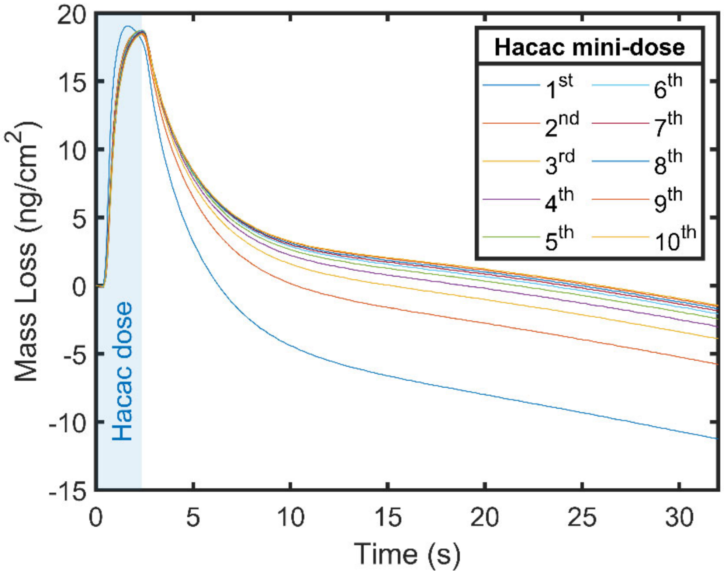

Figure 1 – QCM response to successive mini-doses of Hacac on HF-exposed Al_2O_3 at 250°C.

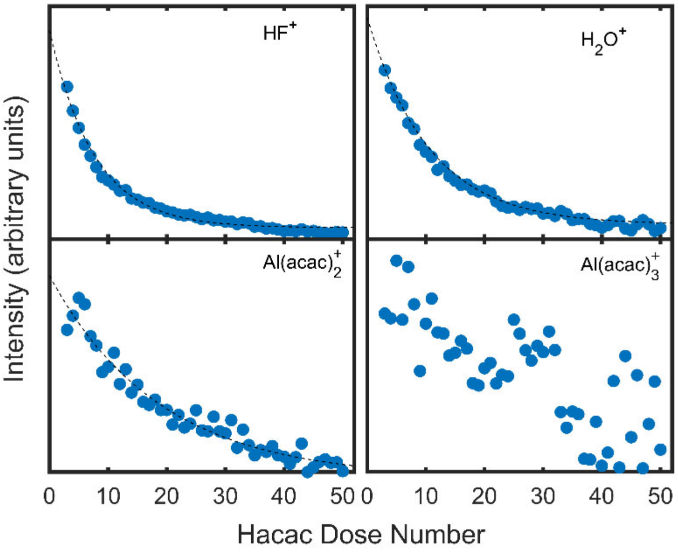

Figure 2 – QMS response to successive mini-doses of Hacac on HF-exposed Al_2O_3 at 250°C.